

The products are Darlington transistor opto-couplers in a plastic SOP4 package. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar phototransistor detector. With the robust coplanar double mold structure, the device provides the most stable isolation feature. The products are widely used in switch mode power supplies, programmable controllers, household appliances and office equipment.

High isolation 3750 VRMS

Operating temperature range -55°C to 110°C

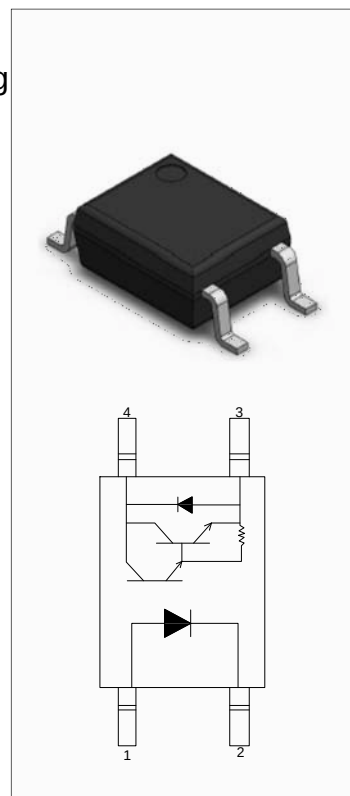
RoHS & REACH Compliance

HBM: H3A; MM: M4; CDM: C3

CQC approved

VDE approved

UL approved



(Temperature=25°C)

Input	Forward Current	I_F	50	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	75	mW
Output	Collector-emitter Voltage	V_{CEO}	80	V
	Emitter-collector Voltage	V_{ECO}	6	V
	Collector Current	I_C	150	mA
	Power Dissipation	P_C	150	mW
Total Power Dissipation		P_{tot}	225	mW
Isolation Voltage		V_{iso}	3750	Vrms
Operating Temperature		T_{opr}	-55~+110	
Junction Temperature		T_j	125	



Storage Temperature	T_{stg}	-55~+125	
Soldering Temperature	T_{sol}	260	

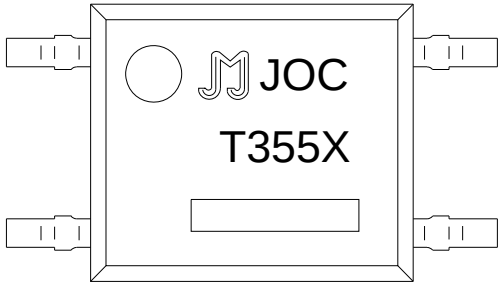
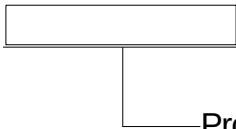
μ

(Temperature=25°C)

Input	Forward Voltage	V_F	$I_F=10mA$	-	1.2	1.5	V
	Reverse Current	I_R	$V_R=6V$	-	-	1	μA
	Terminal Capacitance	C_t	$V=0,$ $f=1MHz$	-	10	-	pF
Output	Collector-Emitter dark current	I_{CEO}	$V_{CE}=20V,$ $I_F=0$	-	-	200	nA
	Collector-Emitter breakdown voltage	BV_{CEO}	$I_C=0.1mA$ $I_F=0$	80	-	-	V
	Emitter-Collector breakdown voltage	BV_{ECO}	$I_E=0.1mA$ $I_F=0$	6	-	-	V
Transfer Characteristics	Current transfer ratio	CTR	$I_F=1mA$ $V_{CE}=2V$	1000	-	7500	%
	Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_F=1mA$ $I_C=10mA$	-	-	1	V
	Isolation resistance	R_{io}	DC500V 40~60%R.H.	10^{12}	-	-	Ω
	Floating Capacitance	C_{io}	$V=0,$ $f=1MHz$	-	0.8	-	pF
	Rise Time	t_r	$V_{CE}=10V,$ $I_C=10mA$ $R_L=100\Omega$	-	40	-	μs
	Fall Time	t_f		-	15	-	μs
	Response Time	t_{on}		-	50	-	μs
		t_{off}		-	15	-	μs

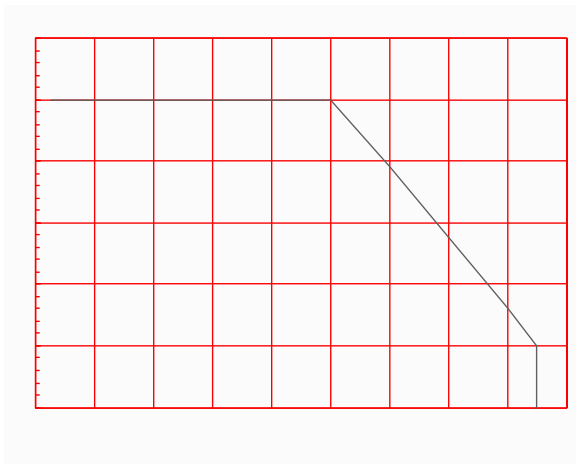


J	OC	T	355	J	-M4	/
JieJie Microelectronics Co., Ltd.	Opto Coupler	Darlington Transistor	Marketization Model	CTR Rank:J/K/L	SOP4	None:T1 R:T2

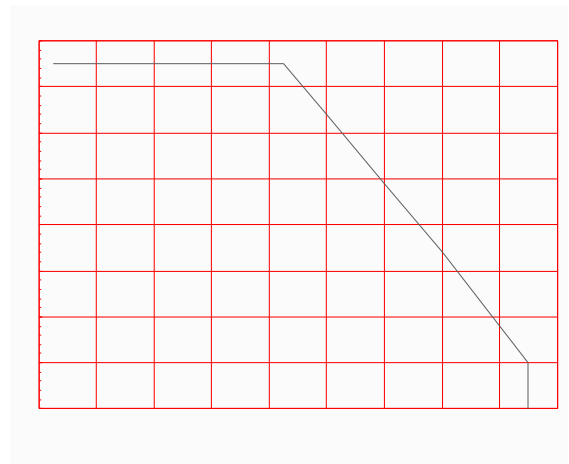
	 Production Information Code
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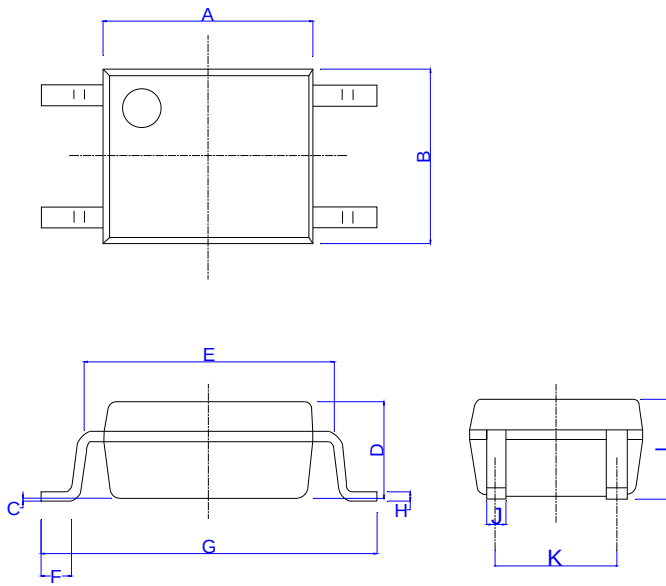


Max. Allowable LED Forward Current vs.
Ambient Temperature

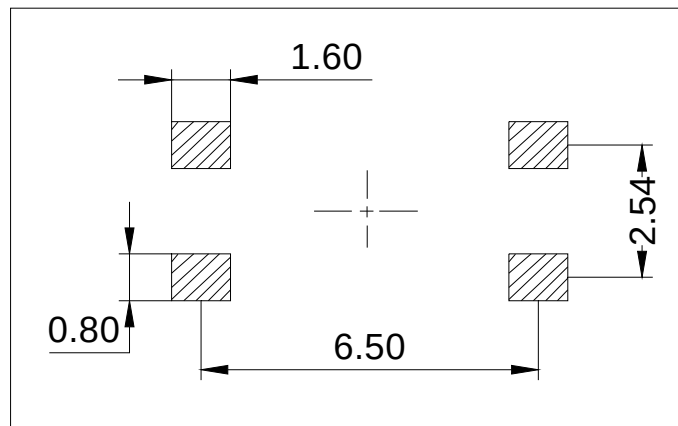


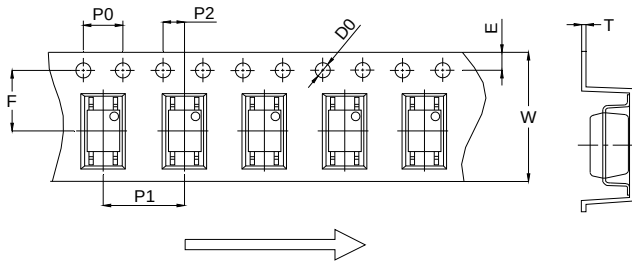
Collector Power Dissipation vs. Ambient
Temperature



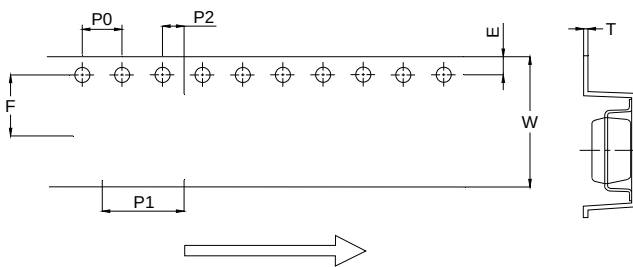


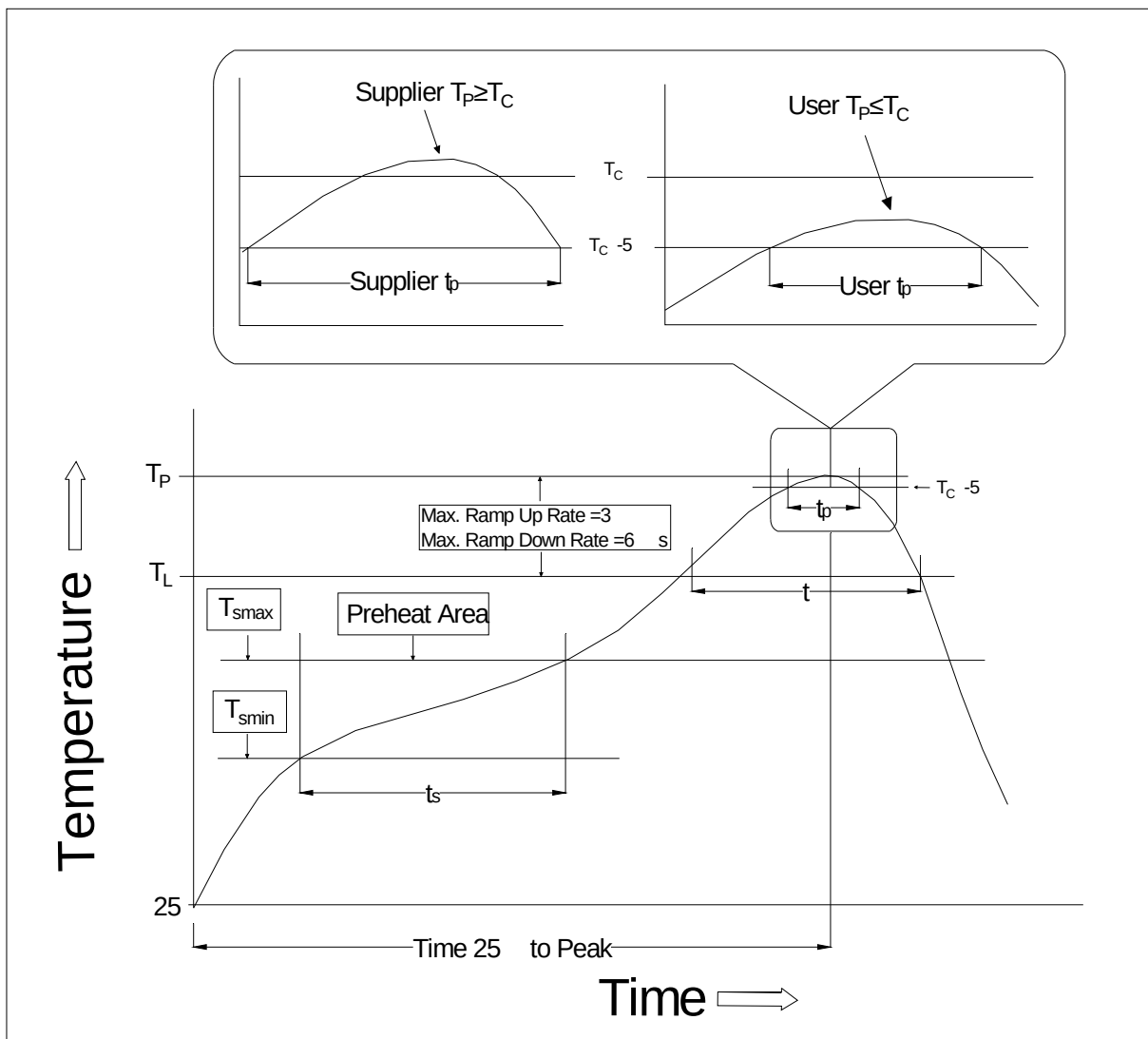
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.80	0.173		0.189
B	3.60		4.20	0.142		0.165
C	0.00		0.20	0.000		0.008
D	1.90		2.30	0.075		0.091
E	5.00		5.60	0.197		0.220
F	0.34		0.94	0.013		0.037
G	6.70		7.30	0.264		0.287
H	0.10		0.30	0.004		0.012
I	2.00		2.40	0.079		0.094
J	0.25		0.55	0.010		0.022
K	2.29		2.79	0.090		0.110





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	4.40	4.50	4.60	0.173	0.177	0.181
T	0.25	0.30	0.35	0.010	0.012	0.014
W	11.90	12.00	12.30	0.469	0.472	0.484





Temperature Min. (T _{smin})	100	150
Temperature Max. (T _{smax})	150	200
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t _L to t _P)	3 /second max.	3 /second max.
Liquidus Temperature (T _L)	183	217
Time (t _L) Maintained Above (T _L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 +0 /-5	260 +0 /-5
Time (t _P) within 5 of 260	10 seconds	10 seconds
Ramp-down Rate (T _P to T _L)	3-6 /second	3-6 /second
Time 25 to Peak Temperature	6 minutes max.	8 minutes max.

